

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

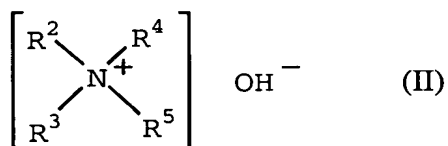
LISTING OF CLAIMS:

1. (original): A cleaning agent composition comprising a nonionic surfactant represented by the following formula (I):



(wherein R^1 represents a linear or branched alkyl group having from 6 to 20 carbon atoms or a linear or branched alkenyl group having from 6 to 20 carbon atoms, EO represents an oxyethylene group, PO represents an oxypropylene group, EO and PO each is bonded by random addition or block addition, x number of EOs and y number of POs are arranged in an arbitrary order, x and y each independently represents an integer of 1 to 20, and $x/(x+y)$ is 0.5 or more) and a quaternary ammonium hydroxide.

2. (original): The cleaning agent composition as claimed in Claim 1, wherein the quaternary ammonium hydroxide is a compound represented by the following formula (II):

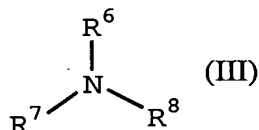


(wherein R^2 , R^3 , R^4 and R^5 each independently represents an alkyl group having from 1 to 6 carbon atoms or a hydroxyalkyl group having from 1 to 6 carbon atoms).

3. (original): The cleaning agent composition as claimed in Claim 2, wherein the quaternary ammonium hydroxide is tetramethylammonium hydroxide.

4. (currently amended): The cleaning agent composition as claimed in ~~any one of~~ Claims 1, which further comprises an alkanolamine.

5. (original): The cleaning agent composition as claimed in Claim 4, wherein the alkanolamine is a compound represented by the following formula (III):



(wherein R⁶ represents a hydroxyalkyl group having from 1 to 4 carbon atoms; and R⁷ and R⁸ each independently represents a hydrogen atom, an alkyl group having from 1 to 4 carbon atoms, a hydroxyalkyl group having from 1 to 4 carbon atoms or an aminoalkyl group having from 1 to 4 carbon atoms, or R⁷ and R⁸ combine to form an alkylene group having from 3 to 6 carbon atoms, and the alkylene group may have an oxygen or nitrogen atom inserted between carbon atoms constituting the main chain).

6. (original): The cleaning agent composition as claimed in Claim 5, wherein the alkanolamine is any one compound selected from the group consisting of monoethanolamine, diethanolamine and triethanolamine.

7. (currently amended): The cleaning agent composition as ~~Claimed~~ claimed in Claim 4, wherein the alkanolamine is contained in an amount of 0.001 to 50 mass% based on the entire amount of the cleaning agent composition.

8. (currently amended): The cleaning agent composition as ~~Claimed~~ claimed in Claim 1, wherein the nonionic surfactant is contained in an amount of 0.0001 to 10 mass% based on the entire amount of the cleaning agent composition.

9. (currently amended): The cleaning agent composition as ~~Claimed~~ claimed in Claim 8, wherein the quaternary ammonium hydroxide is contained in an amount of 0.001 to 30 mass% based on the entire amount of the cleaning agent composition.

10. (original): A method for cleaning a semiconductor wafer, comprising the steps of:

(i) cleaning the wafer using the cleaning agent composition as claimed in any one of Claims 1 to 9; and

(ii) cleaning the wafer using a composition containing ammonia and hydrogen peroxide.

11. (original): The method for cleaning a semiconductor wafer as claimed in Claim 10, wherein the degreasing and removal of particles on the semiconductor wafer surface are performed in the step (i).

12. (currently amended): The method for cleaning a semiconductor wafer as ~~Claimed~~ claimed in Claim 11, wherein the removal of particles on the semiconductor wafer surface are performed in the step (ii).

13. (original): A method for producing a semiconductor wafer, comprising the steps of:

lapping the wafer surface;

specularly polishing the wafer surface;

cleaning the wafer using the cleaning agent composition as claimed in any one of Claims 1 to 9; and

cleaning the wafer using a composition containing ammonia and hydrogen peroxide.

14. (original): A semiconductor wafer produced by the production method as claimed in Claim 13.

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15. (currently amended): The semiconductor wafer as claimed in Claim 14 wherein the number of particles attached to the wafer surface and having a particle size of 0.2 μm or more is 130 or less per 100 cm^2 of the wafer surface.

16. (original): The semiconductor wafer as claimed in Claim 14, wherein the semiconductor wafer is a silicon wafer, a gallium-arsenic wafer, a gallium-phosphorus wafer or an indium-phosphorus wafer.

17. (original): The semiconductor wafer as claimed in Claim 16, wherein the semiconductor wafer is a silicon wafer and the surface roughness (Ra) is 0.2 nm or less.

18. (original): The semiconductor wafer as claimed in Claim 16, wherein the semiconductor wafer is gallium-arsenic wafer and the surface roughness (Ra) is 0.4 nm or less.